AC6323A Datasheet

Zhuhai Jieli Technology Co.,LTD

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AC6323A Features

High performance 32-bit RISC CPU

- RISC 32-bit CPU
- DC-96MHz operation
- 73KB data RAM
- 8KB I-cache 2way
- 1KB Rocache 1way
- 64 Vectored interrupts
- 8 Levels interrupt priority

Flexible I/O

- 13 GPIO pins
- All GPIO pins can be programmable as input or output individually
- All GPIO pins are internal pull-up/pull-down selectable individually
- CMOS/TTL level schmitt triggered input
- External wake up/interrupt on all GPIOs

Peripheral Feature

- One Full Speed USB OTG controller
- Four Multi-function 32-bit timers, support capture and PWM mode
- Three full-duplex advanced UART(DMA)
- Three SPI interface supports host and device mode (DMA)
- One IIC interface supports host and device mode
- RTC, with alarm clock and time base to wake up the chip
- 16-bit PWM generator for motor driving
- Three IQ Encoder
- 8 channels 10-bit ADC

- 1 channel 8 levels Low Power Detector
- Embedded PMU support low power mode
- 2 Crystal Oscillator
- Watchdog
- Power-on reset

Bluetooth Feature

- CMOS single-chip fully-integrated radio and baseband
- Compliant with Bluetooth
 V5.4+BR+EDR+BLE specification
- Bluetooth Piconet and Scatternet support
- Meet class2 and class3 transmitting power requirement
- Support GFSK and π/4 DQPSK all packet types
- Maximum +8dBm transmitting power
- EDR receiver with -93dBm sensitivity
- Support a2dp\avctp\avdtp\avrcp\hfp\spp\smp\ att\gap\gatt\rfcomm\sdp\l2cap profile

Power Supply

- LDOIN is 4.5V to 5.5V
- **VBAT** is 1.8V to 4.5V
- **VDDIO** is 1.8V to 3.4V

Packages

QFN20

Temperature

- Operating temperature: -40°C to +85°C
- Storage temperature: -65°C to +150°C

1. Block Diagram

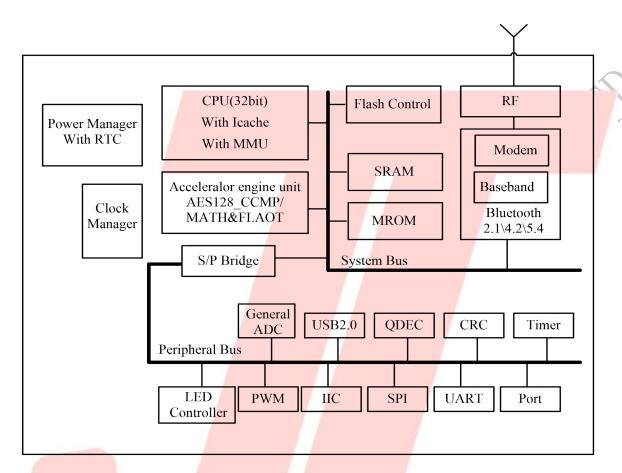


Figure 1-1 AC6323A_QFN20 Block Diagram

2. Pin Definition

2.1 Pin Assignment

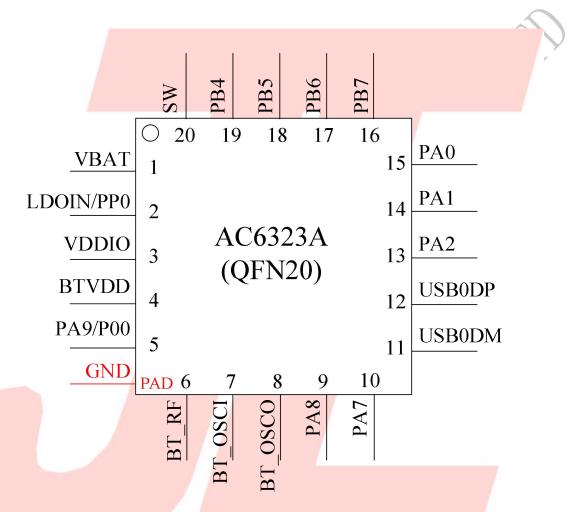


Figure 2-1 AC6323A QFN20 Package Diagram

2.2 Pin Description

Table 2-1 AC6323A_QFN20 Pin Description

PIN NO.	Name	I/O Type	Function	Other Function
1	VBAT	P	LDO Power	-
2	LDOIN/PP0	Р	Charge Power 5V	PWM3: Timer3 PWM Output; UART0_TXD: Uart0 Data Out(D); UART0_RXD: Uart0 Data In(D);
3	VDDIO	P	IO Power 3.3V	-
4	BTAVDD	P	Core Power	-
5	PA9	I/O	GPIO (pull up)	Long Press Reset; ADC8: ADC Channel 8;
3	P00	I/O	GPIO (High Voltage)	
6	BT_RF	-	RF Antenna	
7	BTOSCI	I	BTOSCI	-
8	BTOSCO	О	BTOSCO	-
9	PA8	I/O	GPIO	TMR3: Timer3 Clock In; SPI1_DOA: SPI1 Data Out(A); IIC_SDA_C: IIC SDA(C); ADC4: ADC Channel 4; UART1_RXC: Uart1 Data In(C); PWMCH1L;
10	PA7	I/O	GPIO	TMR1: Timer1 Clock In; SPI1_CLKA: SPI1 Clock(A); IIC_SCL_C: IIC SCL(C); ADC3: ADC Channel 3; UART1_TXC: Uart1 Data Out(C); PWMCH1H;
11	USB0DM	I/O	GPIO (pull down)	SPI2_DOB: SPI2 Data Out(B); IIC_SDA_A: IIC SDA(A); ADC11: ADC Channel 11; UART1_RXD: Uart1 Data In(D);

		1		1
				SPI2_CLKB: SPI2 Clock(B);
12	USB0DP	I/O	GPIO	IIC_SCL_A: IIC SCL(A);
12	CSBODI	1/0	(pull down)	ADC10: ADC Channel 10;
				UART1_TXD: Uart1 Data Out(D);
				CAP3: Timer3 Capture;
12	DAG	1/0	CDIO	Q-decoder0_1;
13	PA2	I/O	GPIO	UART0_RXC: Uart0 Data In(C);
				UART1_RTS;
		1		PWM0: Timer0 PWM Output;
				Q-decoder0_0;
14	PA1	I/O	GPIO	ADC0: ADC Channel 0;
				UART0_TXC: Uart0 Data Out(C);
				UART1_CTS;
				CLKOUT1;
1.5	DAG	1/0	GPIO	UART2_TXB: Uart2 Data Out(B);
15	PA0	I/O	(High Voltage)	UART2_RXB: Uart2 Data In(B);
				РWMCH0Н;
17	DD7	I/O	GPIO	SPI2_DOA: SPI2 Data Out(A);
16	PB7	I/O	(High Voltage)	UART2_RXC: Uart2 Data In(C);
			y e	SPI2_CLKA: SPI2 Clock(A);
17	DD.C	1/0	CDIO	ADC12: ADC Channel 12;
17	PB6	I/O	GPIO	UART2_TXC: Uart2 Data Out(C);
				TMR3CK;
			CDIO	SPI2_DIA: SPI2 Data In(A);
18	PB5	I/O	GPIO	UART1_RXA: Uart1 Data In(A);
			(High Voltage)	PWMCH3L;
				TMR2: Timer2 Clock In;
				Q-decoder2_0;
10	DC 4	1/0	CPIO	SPI1_DIB: SPI1 Data In(B);
19	PB4	I/O	GPIO	ADC9: ADC Channel 9;
				UAR1_TXA: Uart1 Data Out(A);
				РWMCH3H;
20-	OW.	T.	DC-DC	
20	SW	P	Switch Pin	-
	Substrate	P	GND	-
	7	l .		

3. Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-40	+85	°C
Tstg	Storage temperature	-65	+150	°C
VBAT	Supply Voltage	-0.3	4.5	V
LDOIN	Charge Input Voltage	-0.3	6	V
VDDIO	3.3V IO Input Voltage	-0.3	3.6	V

Note: The chip can be damaged by any stress in excess of the absolute maximum ratings listed below

3.2 Recommended Operating Conditions

Table 3-2

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
VBAT	Voltage Input	1.8	3.7	4.5	V	_
LDOIN	Voltage Input	4.5	5.0	5.5	V	_
VDDIO	Voltage output	1.8	3.0	3.4	V	VBAT= 4.2V, 60mA loading
BTAVDD	Voltage output	1	1.3	1.4	V	DC-DC mode: 40mA loading
I _{VDDIO}	Loading current	1	_	60	mA	VBAT = 4.2V

3.3 Battery Charge

Table 3-3

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
LDOIN	Charge Input Voltage	4.5	5	5.5	V	-
V _{Charge}	Charge Voltage	4.15	4.2	4.25	V	-
I_{Charge}	Charge Current	20		200	mA	Charge current at fast charge mode
I_{Trikl}	Trickle Charge Current	20	45	70	mA	V_{BAT} $<$ V_{Trikl}

3.4 IO Input/Output Electrical Logical Characteristics

Table 3-4

IO input ch	IO input characteristics									
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
V _{IL}	Low-Level Input Voltage	-0.3	-	0.3* VDDIO	V	VDDIO = 3.3V				
$V_{ m IH}$	High-Leve <mark>l Input</mark> Volta <mark>ge</mark>	0.7* VDDIO	-	VDDIO+0.3	V	VDDIO = 3.3V				
IO output	characterist <mark>ics</mark>									
V_{OL}	Low-Level Output Voltage	_	_	0.33	V	VDDIO = 3.3V				
V_{OH}	High-Level Output Voltage	2.7	-	7-/	V	VDDIO = 3.3V				

3.5 Internal Resistor Characteristics

Table 3-5

	Port	Drive Strength	Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment
	PA1-PA9, PB4,PB6,	drive_select[11] 24mA drive_select[10] 24mA (with 120ohm res) drive_select[01] 8mA drive_select[00] 8mA (with 120ohm res)	10K	10K	1. PA9&PB2 default pull up 2. USB0DM&USB0DP default pull down 3. Internal pull-up/pull-down
	PA0,PB5, PB7	8mA	10K	10K	resistance accuracy ±20% 4.PA0,PB5,PB7 can pull-up resistance to 5V
L	USB0DP	4mA	1.5K	15K	resistance to 5 v
	USB0DM	4mA	180K	15K	

3.6 BT Characteristics

3.6.1 Transmitter

Basic Rate

Table 3-6

Paramet	er	Min	Тур	Max	Unit	Test Conditions
RF Transmit	Power	-	4	6	dBm	
RF Power Contr	ol Range	-	20	-	dB	25°C,
20dB Bandy	vidth		950	7-7	KHz	Power Supply
In-band spurious	$F=F_0\pm 1MHz$	4	-20	/ / -	dBm	VBAT=3.7V
Emissions	$F=F_0\pm 2MHz$	/-	-45	-	dBm	2441MHz
(BQB Test Mode	$F=F_0\pm 3MHz$	-	-35	/ -	dBm	DH5
RF_Tx Power=4dBm)	$F=F_0\pm>3MHz$	-	-40	-	dBm	, D11.

Enhanced Data Rate

Table 3-7

Paramete	er	Min	Тур	Max	Unit	Test Conditions
Relative Po	wer	-	-1	-	dB	
π/4 DOPSK	DEVM RMS	-	4	-	%	25°C,
	DEVM 99%	- /	12	- /	%	Power Supply
Modulation Accuracy	DEVM Peak	- /	9	- /	%	
In-band spurious	F=F ₀ ±1MHz	-	-4	- /	dBm	VBAT=3.7V
Emissions	F=F ₀ ±2MHz	7/	-30	7	dBm	2441MHz
(BQB Test Mode	$F=F_0\pm 3MHz$	7-/	-30		dBm	2DH5
RF_Tx Power=4dBm)	$F=F_0\pm>3MHz$	7 1	-37	-	dBm	

3.6.2 Receiver

Basic Rate

Table 3-8

Paramete	r	Min	Тур	Max	Unit	Test Conditions
Sensitivit	y	-	-91	-	dBm	
Co-channel Interferen	ice Rejection	-	6	-	dB	25°C,
	+1MHz	-	-7	-	dB	Power Supply
	-1MHz		-7	-	dB	
Adjacent Channel	+2MHz	-	-37	-	dB	VBAT=3.7V
selectivity C/I -2MHz		- //	-39		dB	2441MHz
	+3MHz	1	-32	/ /-	dB	DH5
	-3MHz	-	-43	-	dB	

Enhanced Data Rate

Table 3-9

Paramete	r	Min	Тур	Max	Unit	Test Conditions
Sensitivit	y	-	-93	-	dBm	
Co-channel Interferer	ace Rejection	-	8	-	dB	25°C,
	+1MHz	-	-14	-	dB	Power Supply
	-1MHz	-	-15	- ,	dB	
Adjacent Channel	+2MHz	- 7	-36	- /	dB	VBAT=3.7V
selectivity C/I	-2MHz	- /	-39	- /	dB	2441MHz
	+3MHz	-/ /	-29	- 7	dB	2DH5
	-3MHz	-/	-43	1	dB	

3.6.3 BLE

1M Data Rate

Table 3-10

Paramete	er	Min	Тур	Max	Unit	Test Conditions
Sensitivit	y	-	-95	-	dBm	
RF Transmit F	Power	-	6.5	8	dBm	
In-band Spurious	M-N =2MHz	-	-35	-	dBm	
Emission	M-N ≥3MHz	-	-33	-	dBm	25°C
	Δfl avg	-	250	-	KHz	Power Supply
Modulation Characteristics	Δf2 99%	-7	210	7 -	KHz	VBAT=3.7V
Characteristics	Δflavg/Δf2avg	4	0.9	/ -	/	2440MHz
Carrier Frequency Offset		-15	- /	+15	KHz	
Frequency Drift		-25	- 7	+25	KHz	
Frequency Dri	ft Rate	-5	-/ //	+5	KHz/50us	

2M Data Rate

Table 3-11

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivity		-	-92	-	dBm	
RF Transmit Power		-	6.5	8	dBm	
In-band Spurious Emission	M-N =4MHz	-	-40	-	dBm	
	M-N =5MHz	-	-40	- ,/	dBm	25℃
	M-N ≥6MHz	-///	-40	-	dBm	Power Supply
Modulation Characteristics	Δfl avg	7- /-	500	7-	KHz	
	Δf2 99%	/-/	430	-	KHz	VBAT=3.7V
	Δflavg/Δf2avg	/ /	0.9	-	/	2440MHz
Carrier Frequency Offset		-20	-	+20	KHz	
Frequency Drift		-25	-	+25	KHz	
Frequency Drift Rate		-5	-	+5	KHz/50us	

Long Range

Table 3-12

Parameter	Min	Тур	Max	Unit	Test Conditions
Sensitivity LE 125K(S8)	-	-102	-	dBm	VBAT=3.7V,25°C
Sensitivity LE 500K(S2)	-	-99	-	dBm	2440MHz

4. Package Information

4.1 QFN20(3mm*3mm)

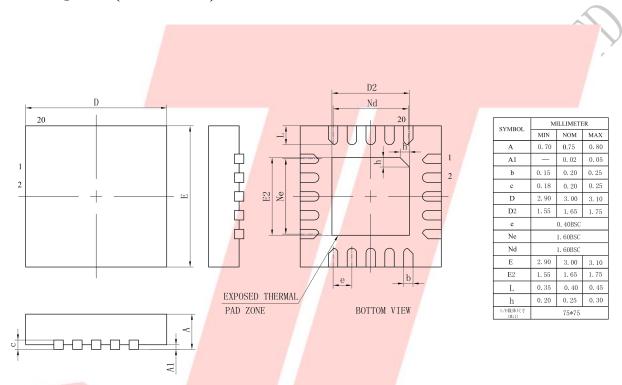
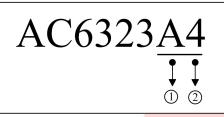


Figure 4-1 AC6323A_QFN20 Package

5. Package Type Specification



- ①Represents different packages
- ②Represents different memory sizes
 - 2: 2Mbit Flash
 - 4: 4Mbit Flash

6. Revision History

Date	Revision	Description
2021.03.06	V1.0	Initial Release
2022.07.19	V1.1	Update Bluetooth Feature
2023.11.24	V1.2	Add BLE parameter
2023.12.13	V1.3	Update Bluetooth Feature